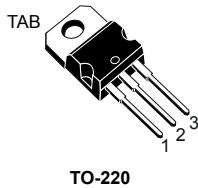
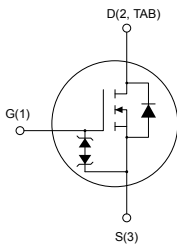


Automotive-grade N-channel 650 V, 102 mΩ typ., 28 A MDmesh DM6 Power MOSFET in a TO-220 package



TO-220


AM01476v1_lab



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STP30N65DM6AG	650 V	115 mΩ	28 A

- AEC-Q101 qualified 
- Fast-recovery body diode
- Lower R_{DS(on)} per area vs previous generation
- Low gate charge, input capacitance and resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

Applications

- Switching applications

Description

This high-voltage N-channel Power MOSFET is part of the MDmesh DM6 fast-recovery diode series. Compared with the previous MDmesh fast generation, DM6 combines very low recovery charge (Q_{rr}), recovery time (t_{rr}) and excellent improvement in R_{DS(on)} per area with one of the most effective switching behaviors available in the market for the most demanding high-efficiency bridge topologies and ZVS phase-shift converters.

Product status link

[STP30N65DM6AG](#)

Product summary

Order code	STP30N65DM6AG
Marking	30N65DM6
Package	TO-220
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	28	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	18	A
$I_{DM}^{(1)}$	Drain current (pulsed)	112	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	223	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	100	V/ns
$di/dt^{(2)}$	Peak diode recovery current slope	1000	A/ μs
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	100	V/ns
T_J	Operating junction temperature range	-55 to 150	$^\circ\text{C}$
T_{stg}	Storage temperature range		

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 28\text{ A}$, $V_{DS}(\text{peak}) < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$.
3. $V_{DS} \leq 520\text{ V}$.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.56	$^\circ\text{C/W}$
R_{thJA}	Thermal resistance, junction-to-ambient	62.5	

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or non-repetitive (pulse width limited by T_J max)	4	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 100\text{ V}$)	600	mJ

2 Electrical characteristics

$T_C = 25\text{ }^\circ\text{C}$ unless otherwise specified

Table 4. On/off-state

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$			5	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$, $T_C = 125\text{ }^\circ\text{C}^{(1)}$			200	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 25\text{ V}$			± 5	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3.25	4.00	4.75	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 10\text{ A}$		102	115	m Ω

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	2000	-	pF
C_{oss}	Output capacitance		-	130	-	pF
C_{rSS}	Reverse transfer capacitance		-	1.5	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }520\text{ V}$, $V_{GS} = 0\text{ V}$	-	339	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$, open drain	-	1.6	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}$, $I_D = 28\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 14. Test circuit for gate charge behavior)	-	46	-	nC
Q_{gs}	Gate-source charge		-	13.5	-	nC
Q_{gd}	Gate-drain charge		-	20	-	nC

1. $C_{oss\text{ eq.}}$ is defined as the constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325\text{ V}$, $I_D = 14\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$	-	17	-	ns
t_r	Rise time		-	3.3	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	46	-	ns
t_f	Fall time		-	8	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		28	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		112	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 28\text{ A}, V_{GS} = 0\text{ V}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 28\text{ A}, di/dt = 100\text{ A}/\mu\text{s},$	-	126		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 60\text{ V}$	-	0.63		μC
I_{RRM}	Reverse recovery current	(see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	10		A
t_{rr}	Reverse recovery time	$I_{SD} = 28\text{ A}, di/dt = 100\text{ A}/\mu\text{s},$	-	220		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 60\text{ V}, T_J = 150\text{ }^\circ\text{C}$	-	2.1		μC
I_{RRM}	Reverse recovery current	(see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	19		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

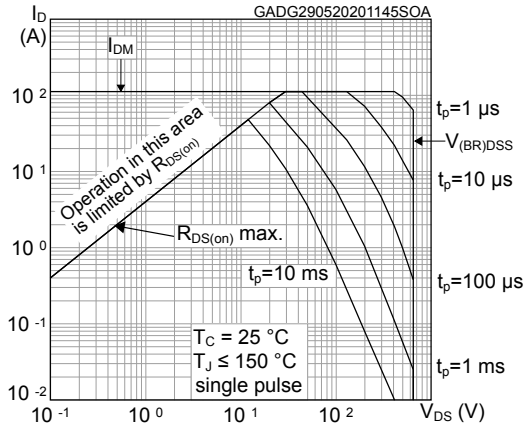


Figure 2. Maximum transient thermal impedance

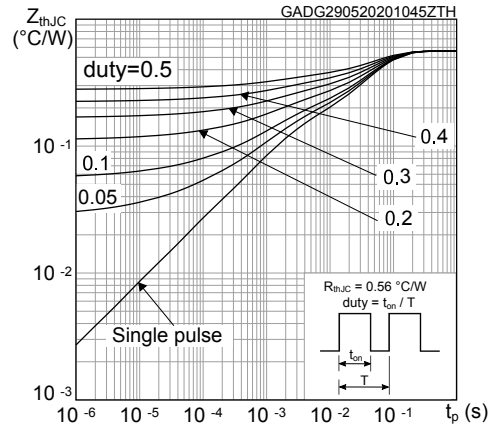


Figure 3. Typical output characteristics

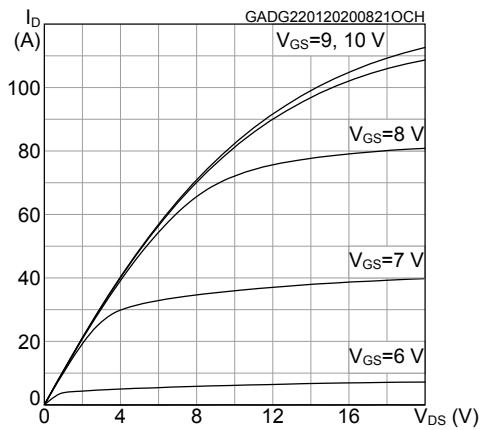


Figure 4. Typical transfer characteristics

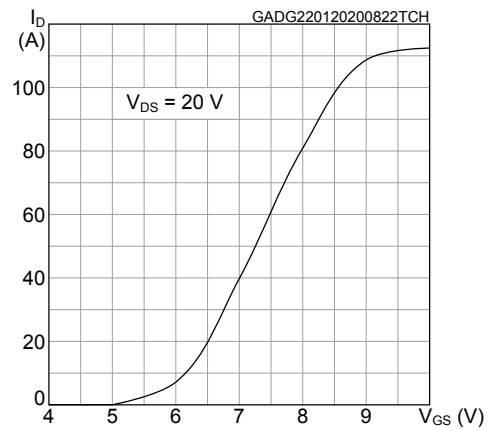


Figure 5. Typical drain-source on-resistance

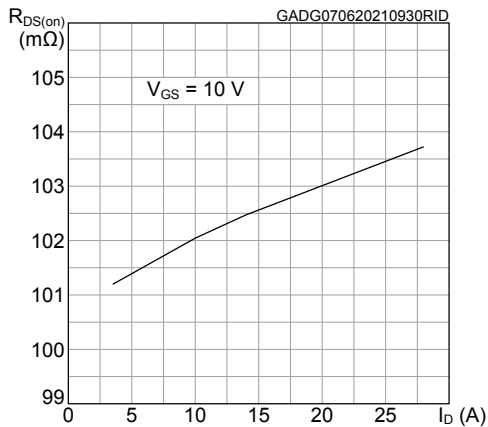


Figure 6. Typical gate charge characteristics

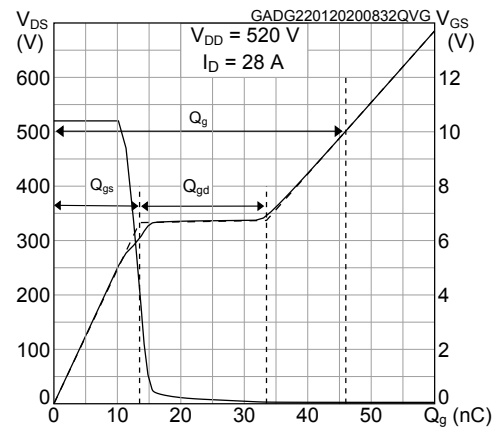


Figure 7. Typical capacitance characteristics

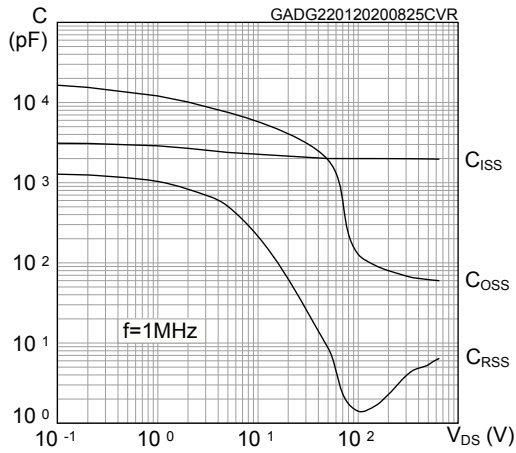


Figure 8. Normalized gate threshold vs temperature

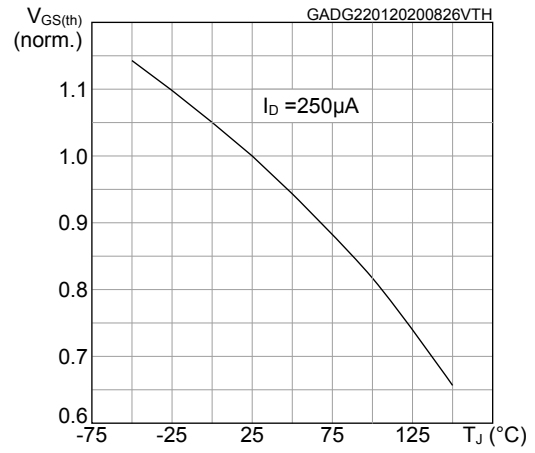


Figure 9. Normalized on-resistance vs temperature

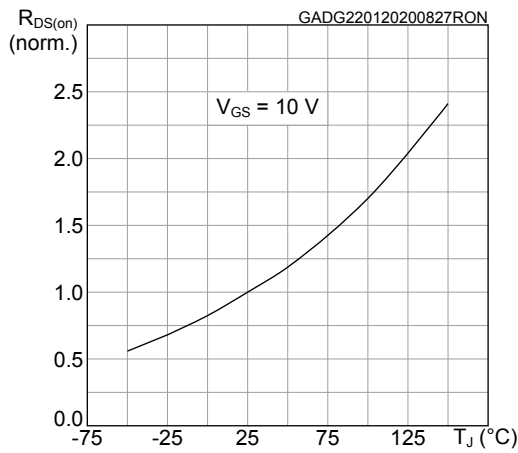


Figure 10. Typical output capacitance stored energy

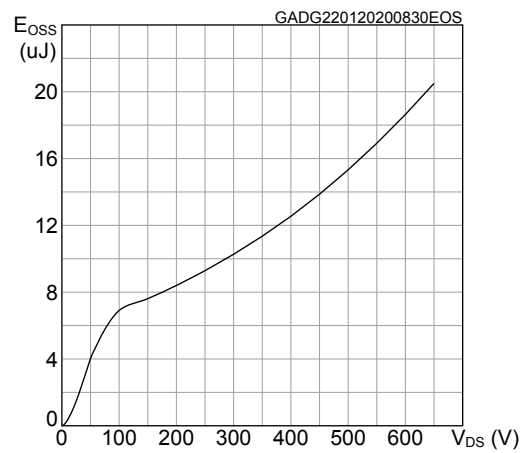


Figure 11. Normalized breakdown voltage vs temperature

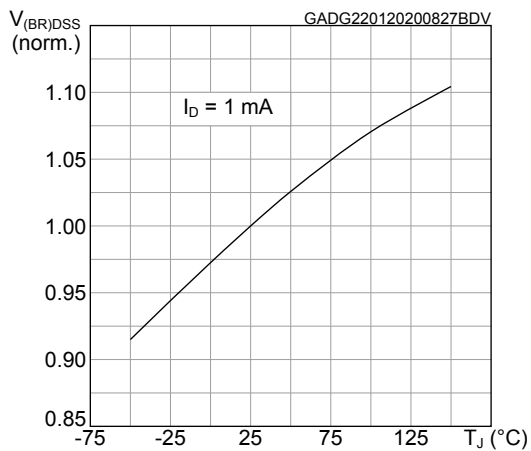
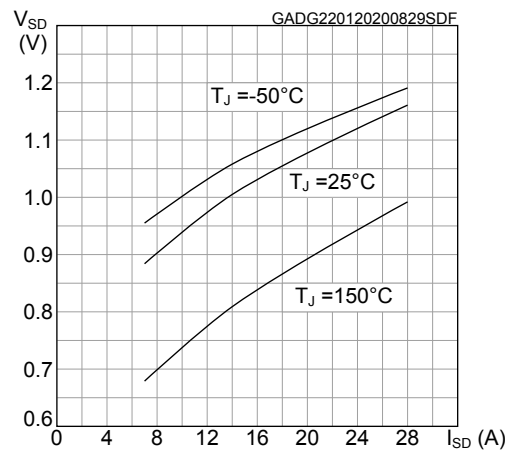
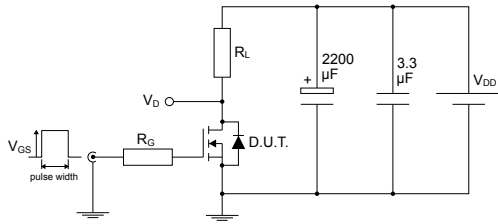


Figure 12. Typical reverse diode forward characteristics



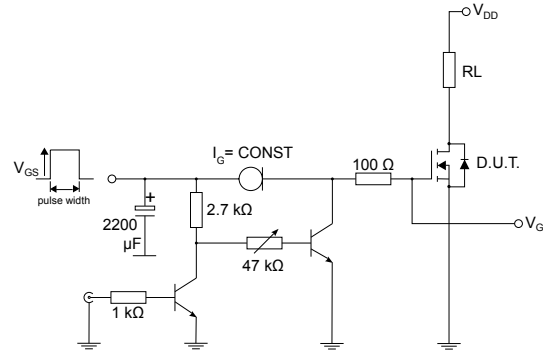
3 Test circuits

Figure 13. Test circuit for resistive load switching times



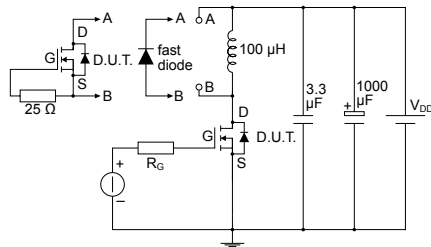
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Figure 14. Test circuit for gate charge behavior



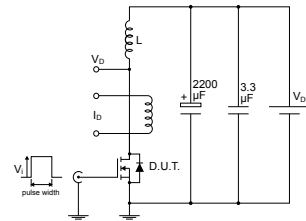
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Figure 15. Test circuit for inductive load switching and diode recovery times



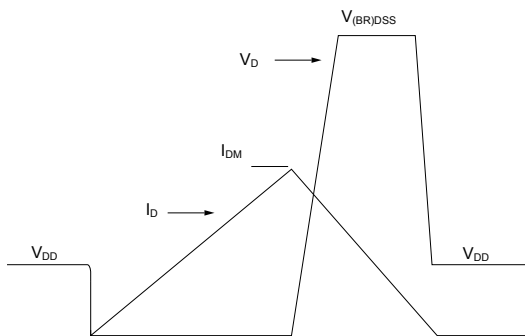
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Figure 16. Unclamped inductive load test circuit



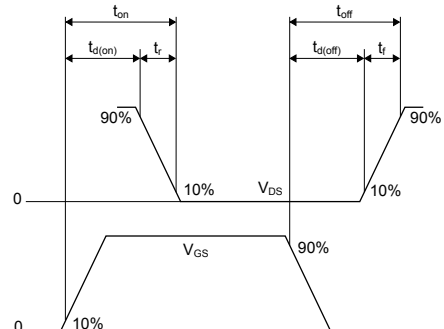
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Figure 17. Unclamped inductive waveform



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Figure 18. Switching time waveform



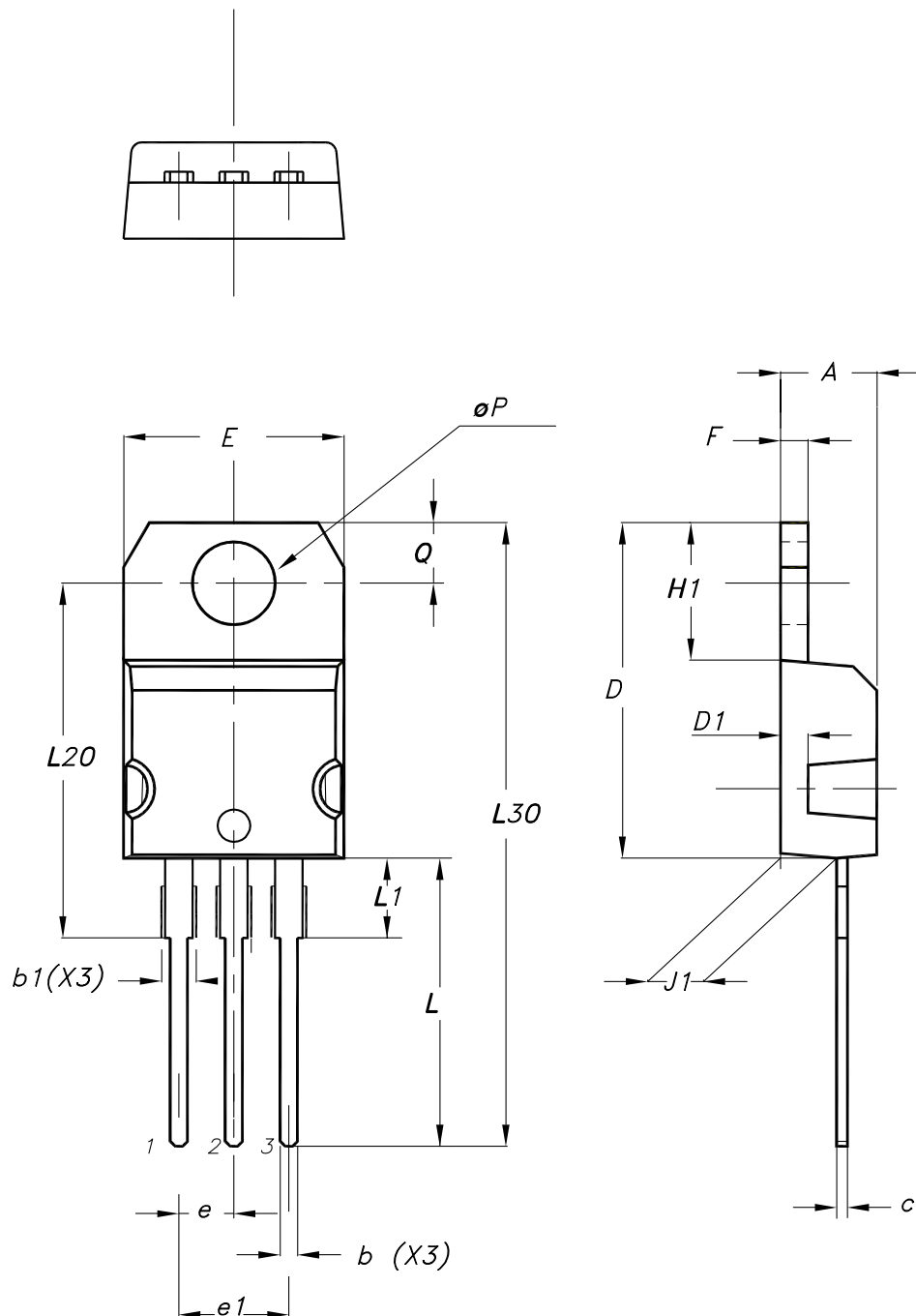
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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-220 type A package information

Figure 19. TO-220 type A package outline



0015988_typeA_Rev_23

Table 8. TO-220 type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95
Slug flatness		0.03	0.10

Revision history

Table 9. Document revision history

Date	Revision	Changes
11-Jun-2020	1	First release.
09-Jun-2021	2	<p>Modified $R_{DS(on)max}$ value on features table.</p> <p>Modified Table 1. Absolute maximum ratings, Table 2. Thermal data, Table 4. On/off-state, Table 6. Switching times.</p> <p>Modified Figure 1. Safe operating area, Figure 2. Maximum transient thermal impedance, Figure 3. Typical output characteristics, Figure 4. Typical transfer characteristics and Figure 5. Typical drain-source on-resistance.</p> <p>Minor text changes.</p>

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